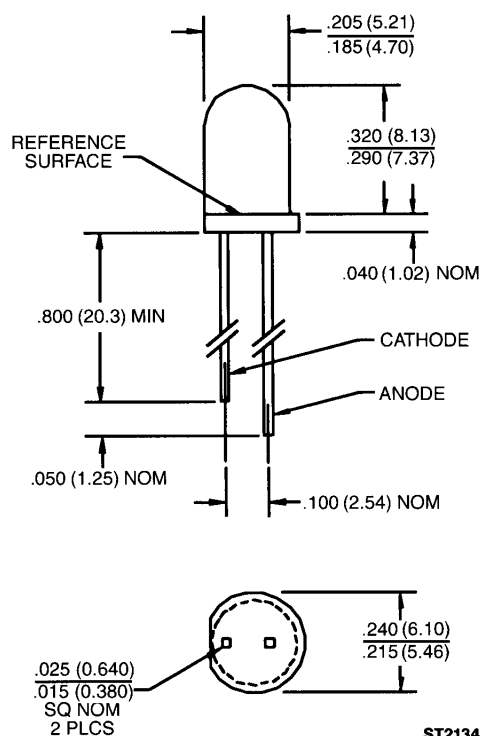




GaAs INFRARED EMITTING DIODE

QED233/234

PACKAGE DIMENSIONS



DESCRIPTION

The QED23X is a 940nm GaAs LED encapsulated in a clear plastic T-1 $\frac{3}{4}$ package.

FEATURES

- Tight production E_o distribution.
- Steel lead frames for improved reliability in solder mounting.
- Good optical-to-mechanical alignment.
- Wide emission angle.
- Mechanical and wavelength matched to QSD12X series phototransistor.
- Plastic package color allows easy recognition from phototransistor.
- Medium and high irradiance level.

NOTES:

1. DIMENSIONS ARE IN INCHES (mm).
2. TOLERANCE IS $\pm .010 (.25)$ UNLESS OTHERWISE SPECIFIED.
3. FLAT DENOTES CATHODE.



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ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

Storage Temperature	-40°C to $+100^\circ\text{C}$
Operating Temperature	-40°C to $+100^\circ\text{C}$
Soldering:	
Lead Temperature (Iron)	240°C for 5 sec. ^(2,3,4,5)
Lead Temperature (Flow)	260°C for 10 sec. ^(2,3,5)
Continuous Forward Current	100 mA
Reverse Voltage	5.0 Volts
Power Dissipation	200 mW ⁽¹⁾

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified) (All measurements made under pulse conditions.)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Forward Voltage	V_F	—		1.50	V	$I_F = 20\text{ mA}$
Reverse Leakage Current	I_R	—		10	μA	$V_R = 5.0\text{ V}$
Peak Emission Wavelength	λ_P	—	940	—	nm	$I_F = 20\text{ mA}$
Emission Angle at $\frac{1}{2}$ Power	θ	—	± 20	—	Degrees	
Radiant Incidence QED233	E_0	0.05		0.25	mW/10° Cone	$I_F = 20\text{ mA}$ ^(6,7)
Radiant Incidence QED234	E_0	0.13		—	mW/10° Cone	$I_F = 20\text{ mA}$ ^(6,7)

NOTES

- Derate power dissipation linearly 2.67 mW/ $^\circ\text{C}$ above 25°C .
- RMA flux is recommended.
- Methanol or Isopropyl alcohols are recommended as cleaning agents.
- Soldering iron tip $\frac{1}{16}$ " (1.6 mm) minimum from housing.
- As long as leads are not under any stress or spring tension.
- Measurement is taken at the end of a single 100 μsec pulse.
- E_0 is a measurement of the average apertured radiant energy incident upon a sensing area 0.444" (11.3 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 2.54" (64.4 mm) from the measurement surface. E_0 is not necessarily uniform within the measurement area.